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Data Sheet N2480, REV.-

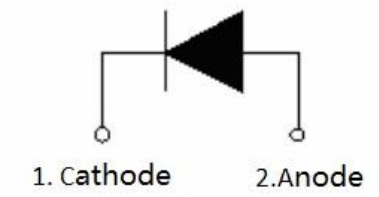
S4D30120H2
1200V SIC POWER SCHOTTKY RECTIFIER

TO-247AC(TO-247-2)

Description

S4D30120H2 is a SiC Schottky rectifier packaged in TO-247AC(TO-247-2) case. The device is high voltage Schottky rectifier that has very low total conduction losses and very stable switching characteristics over temperature extremes. The S4D30120H2 is ideal for energy sensitive, high frequency applications in challenging environments.

Circuit Diagram



Features

- 175°C T_J operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- "-A" is an AEC-Q101 qualified device
- Pb − Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

Applications

- Solar inverters
- UPS (Uninterruptible Power Supply)
- PFC (Power Factor Correction)
- EV charger modules
- Industrial power supply

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Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	1200	V
Average Rectified Forward Current	$I_{F(AV)1}$	T_C =25°C	88	A
	$I_{F(AV)2}$	T_C =150°C	30	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM1}	10ms, Half Sine pulse, T_C =25°C	233	A
	I_{FSM2}	10ms, Half Sine pulse, T_C =110°C	209	A
Repetitive Peak Forward Surge Current	I_{FRM1}	10ms, Half Sine pulse , T_C =25°C	121	A
	I_{FRM2}	10ms, Half Sine pulse , T_C =110°C	68	A
Power Dissipation	P_{tot1}	T_C =25℃	441	W
	P_{tot2}	T_C =110℃	191	W

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 30A, Pulse, T_J = 25 °C	1.55	1.8	V
	V_{F2}	@ 30A, Pulse, T_J = 175 °C	2.3	3.0	V
Reverse Current*	I_{R1}	@V_R = rated V_R T_J = 25 °C	1	25	uA
	I_{R2}	@V_R = rated V_R T_J = 175 °C	10	200	uA
Junction Capacitance	C_T	VR=0V, f=1MHz, Tj=25℃,	2030	-	pF
Reverse Recovery Charge	Q_c	V_R = 800 V, T_J =25°C	166.4	-	nC
Capacitance Stored Energy	E_C	V_R = 800 V, T_J =25°C	87.9	-	μJ

* Pulse width < 300 μs, duty cycle < 2%

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Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +175	°C
Storage Temperature	T_{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation, Tj=25℃	0.34	°C/W

Electrostatic Discharge (ESD) Classifications:

Parameter	Symbol	Value
Human Body Model	HBM	Class 3B (≥ 8000 V)
Charge Device Model	CDM	Class C3 (≥ 1000 V)

Ordering Information

Device	Package	Shipping
S4D30120H2	TO-247AC(TO-247-2)	25pcs / tube

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Ratings and Characteristics Curves

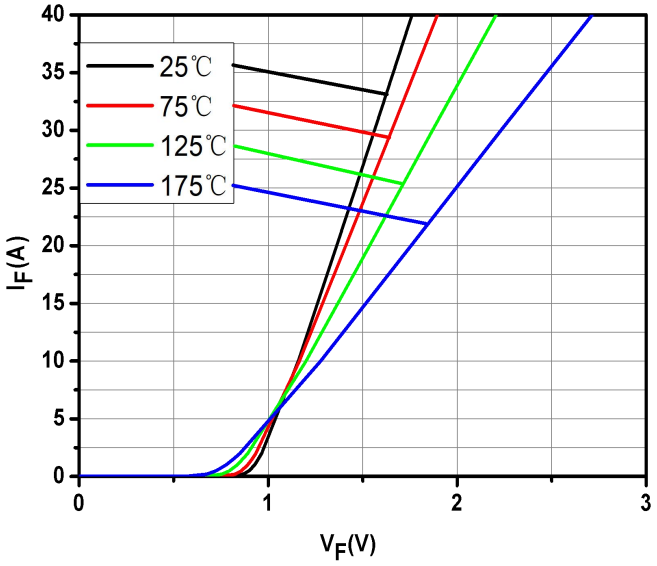

Fig.1-Typical Forward Voltage Characteristics

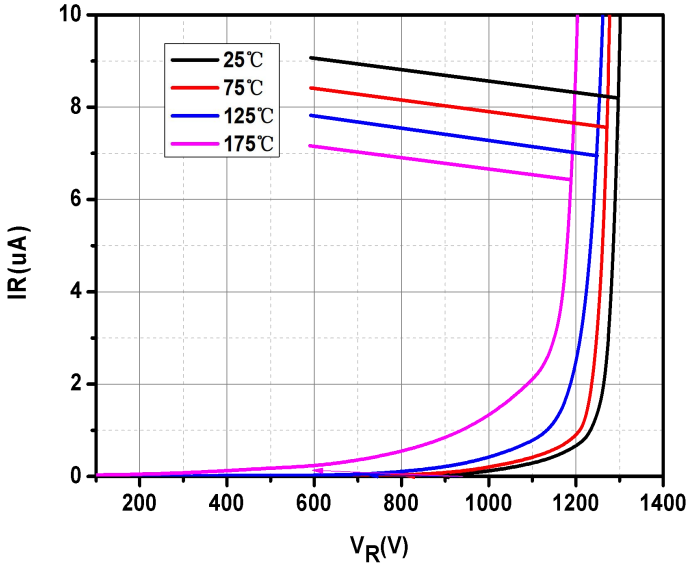

Fig.2-Typical Reverse Characteristics

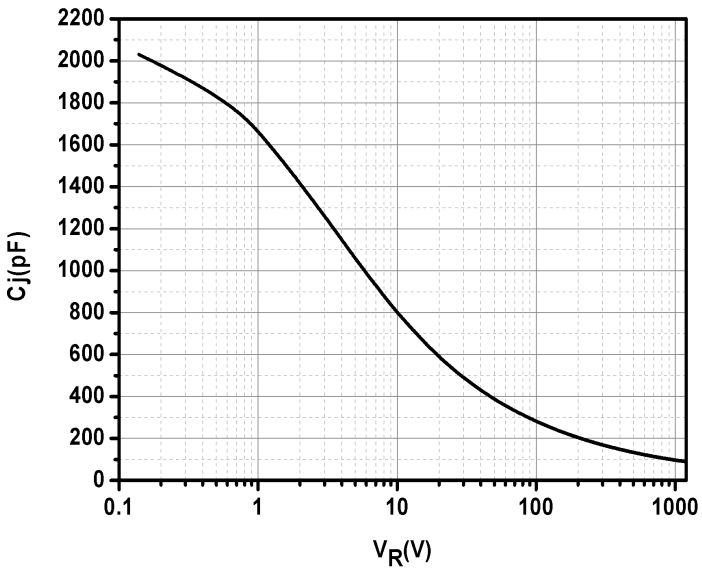

Fig.3-Capacitance vs. Reverse Voltage

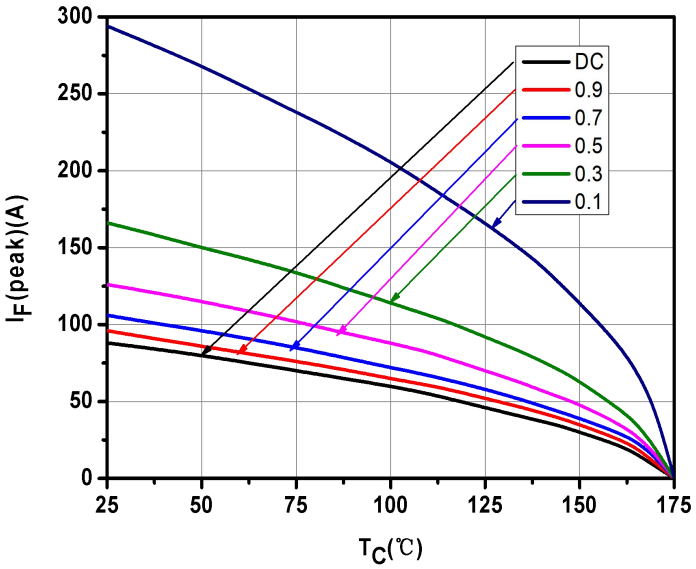

Fig.4-Current Derating

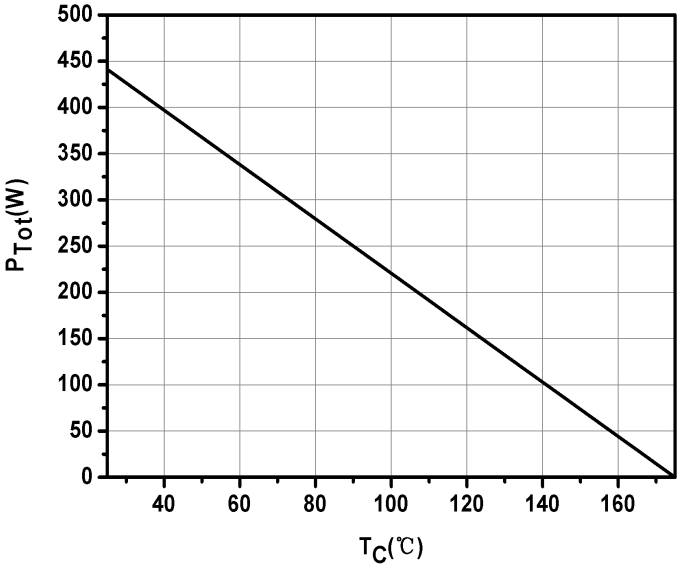

Fig.5-Power Derating

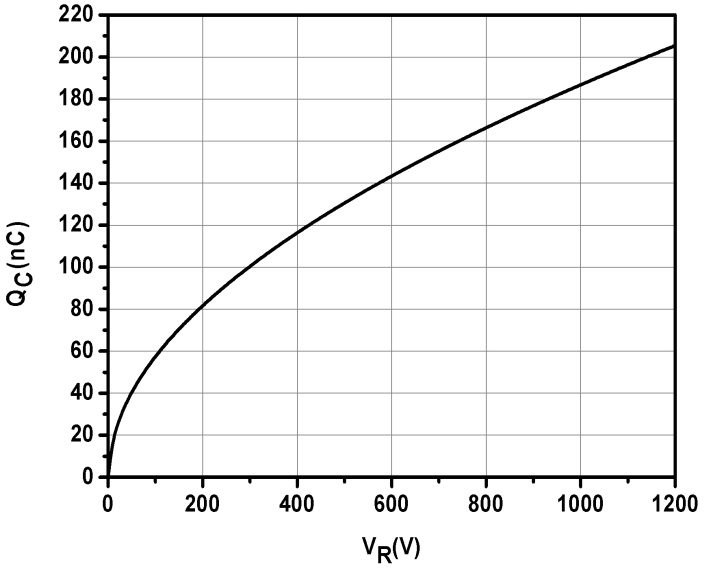

Fig.6-Total Capacitance Charge vs. Reverse Voltage

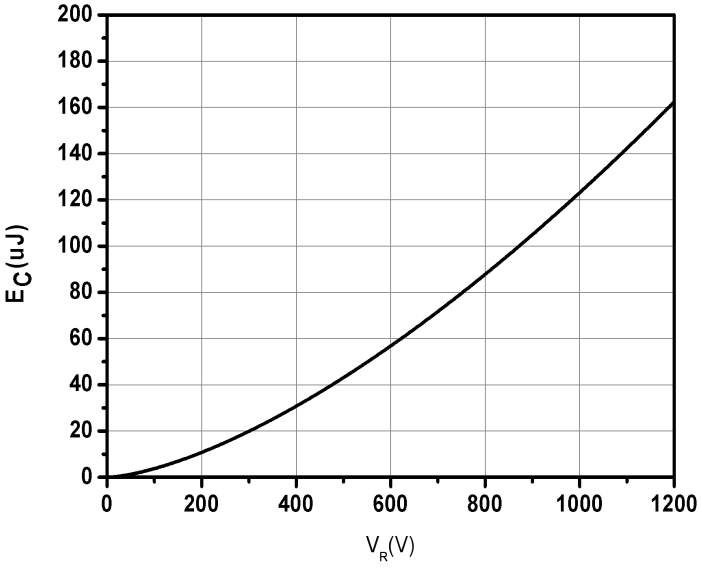

Fig.7-Capacitance Stored Energy

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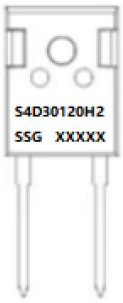
Marking Diagram

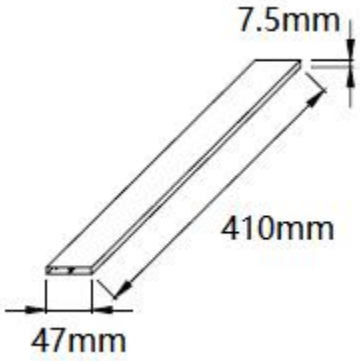


Where XXXXX is YYWWL

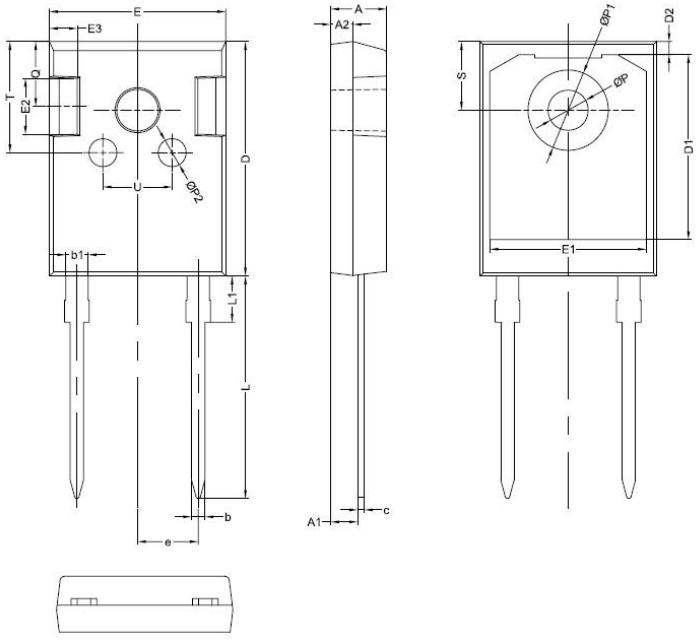
S4D	= Device Type
H	= Package type
30	= Forward Current (30A)
120	= Reverse Voltage (1200V)
SSG	= SSG
YY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Tube Specification(TO-247AC(TO-247-2)



Mechanical Dimensions TO-247AC(TO-247-2)



SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.80	5.00	5.20
A1	2.20	2.41	2.61
A2	1.90	2.00	2.10
b	1.10	1.20	1.35
b1	1.80	2.00	2.20
c	0.50	0.60	0.75
D	20.30	21.00	21.20
D1		16.58	
D2		1.17	
E	15.60	15.80	16.00
E1		14.02	
E2		5.00	
E3		2.50	
e		5.44	
L	19.42	19.92	20.42
L1		4.13	
P	3.50	3.60	3.70
P1	7.1	7.19	7.40
P2		2.50	
Q		5.80	
S	6.05	6.15	6.25
T		10.00	
U		6.20	

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